



# 30V N-Channel Power MOSFET

TO-252 (DPAK)

# 2 65 2 3

### Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

# **Key Parameter Performance**

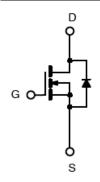
Param	Parameter		Unit	
$V_{ t DS}$		30	V	
R <sub>DS(on)</sub> (max)	$V_{GS} = 10V$	6	mΩ	
	$V_{GS} = 4.5V$	9		
$Q_g$		11.1	nC	

# **Ordering Information**

Ordering code	Package	Packing	
TSM060N03CP ROG	TO-252	2.5kpcs / 13" Reel	
Note: Hologon from according to IEC 61240-2-21 definition			

**Note:** Halogen-free according to IEC 61249-2-21 definition

# **Block Diagram**



N-Channel MOSFET

# **Absolute Maximum Ratings** (T<sub>C</sub>=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30	V	
Gate-Source Voltage		V <sub>GS</sub>	±20	V	
Cantinuous Drain Current	T <sub>C</sub> =25°C		80	А	
Continuous Drain Current	T <sub>C</sub> =100°C	I <sub>D</sub>	51	А	
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	320	А	
Single Pulse Avalanche Energy (Note 2)		E <sub>AS</sub>	88	mJ	
Single Pulse Avalanche Current (Note 2)		I <sub>AS</sub>	42	А	
Total Power Dissipation	@ T <sub>C</sub> =25°C	1	54	W	
	Derate above T <sub>C</sub> =25°C	$P_{D}$	0.43	W/ºC	
Operating Junction Temperature		T <sub>J</sub>	150	°C	
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C	

## **Thermal Performance**

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R <sub>eJC</sub>	2.3	°C/W
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	62	°C/W



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**Electrical Specifications** (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static		- 1		ı		
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	30			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 20A$			4.8	6	mΩ
	$V_{GS} = 4.5V, I_D = 10A$	$R_{DS(ON)}$		6.5	9	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.6	2.5	V
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$				1	μΑ
	V <sub>DS</sub> = 24V, T <sub>J</sub> = 125°C	- I <sub>DSS</sub>			10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Forward Transconductance	$V_{DS} = 10V, I_{D} = 10A$	g <sub>fs</sub>		18		S
Dynamic						
Total Gate Charge <sup>(Note 3,4)</sup>		Qg		11.1		nC
Gate-Source Charge <sup>(Note 3,4)</sup>	$V_{DS} = 15V, I_{D} = 20A,$	$Q_gs$		1.85		
Gate-Drain Charge <sup>(Note 3,4)</sup>	$V_{GS} = 4.5V$	$Q_{gd}$		6.8		
Input Capacitance		C <sub>iss</sub>		1160		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C <sub>oss</sub>		200		pF
Reverse Transfer Capacitance	f = 1MHz	C <sub>rss</sub>		180		
Gate Resistance	f = 1MHz	$R_g$		2.5		Ω
Switching						
Turn-On Delay Time <sup>(Note 3,4)</sup>		t <sub>d(on)</sub>		7.5		
Turn-On Rise Time <sup>(Note 3,4)</sup>	V <sub>DD</sub> =15V , V <sub>GS</sub> =10V ,	t <sub>r</sub>		14.5		
Turn-Off Delay Time <sup>(Note 3,4)</sup>	$R_G=3.3\Omega$ , $I_D=-15A$	t <sub>d(off)</sub>		35.2		ns
Turn-Off Fall Time <sup>(Note 3,4)</sup>		t <sub>f</sub>		9.6		
Source-Drain Diode Ratings and C	haracteristic	- 1		l		
Continuous Drain-Source Diode		Is			80	Α
Pulse Drain-Source Diode		I <sub>SM</sub>			320	Α
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = 1A$	V <sub>SD</sub>			1	V

### Note:

- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2.  $V_{DD}$ =25V,  $V_{GS}$ =10V, L=0.1mH,  $I_{AS}$ =42A,  $R_{G}$ =25 $\Omega$ , Starting  $T_{J}$ =25 $^{\circ}$ C
- 3. The data tested by pulsed , pulse width  $\leq$ 300µs, duty cycle  $\leq$ 2%
- 4. Essentially independent of operating temperature.

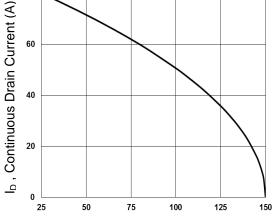


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### **Electrical Characteristics Curve**

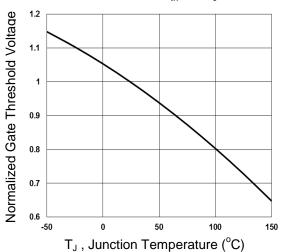


Continuous Drain Current vs. Tc

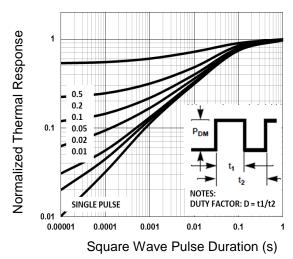


## Normalized V<sub>th</sub> vs. T<sub>J</sub>

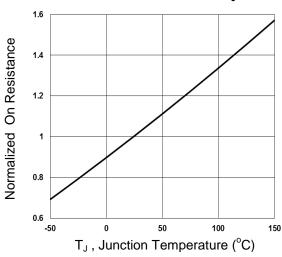
T<sub>C</sub>, Case Temperature (°C)



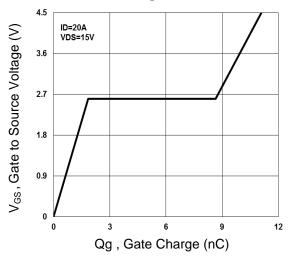
### **Normalized Transient Impedance**



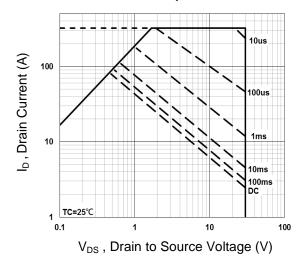
Normalized RDSON vs. T<sub>J</sub>



**Gate Charge Waveform** 



### **Maximum Safe Operation Area**



Version: B1807

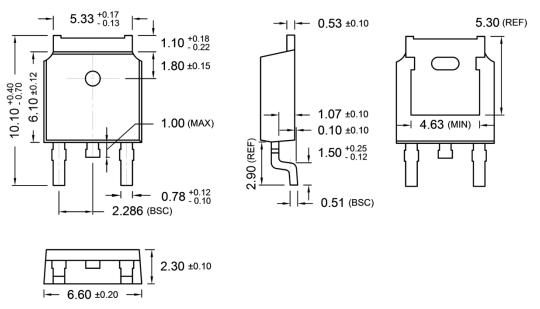
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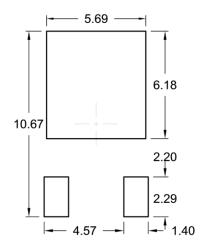


# **TO-252 Mechanical Drawing**



**Unit: Millimeters** 

## SUGGESTED PAD LAYOUT (Unit: Millimeters)



# **Marking Diagram**





# TSM060N03CP 30V N-Channel Power MOSFET

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